



Silicon Carbide Schottky Diode

V_{RRM}	650 V
I_F 127°C	6 A
Q_C	25 nC

Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery voltage
- Essentially no switching losses
- Reduction of heat sink requirements
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical



	SYMBOL	UNIT	VALUE
Reverse Voltage Surge Peak 4 Tc 125 °C	V_{RSM}	V	650
Reverse Voltage DC 4 Tc 125 °C	V_{DC}	V	650
Continuous Forward Current 4 Tc 25 °C	I_F	A	12
Continuous Forward Current 4 Tc 175 °C			6
Non-repetitive peak forward surge current 4 Tc 125 °C tp 10ms <al Z Sine Ka je	I_{FSM}	A	65
Power Dissipation 4 Tc 25 °C	P_{TOT}	K	1
Power Dissipation 4 Tc 110 °C			1
Peak Value 4 Tc 125 °C tp 10ms	i_{2dt}	A	



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Electrical Characteristics

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	Typ.	Max.
Forward voltage drop	V_F	V	$I_F=6A, T_J=25^{\circ}C$	1.31	1.5
			$I_F=6A, T_J=175^{\circ}C$	1.65	-
Reverse leakage current	I_R	μA	$V_R=650V, T_J=25^{\circ}C$	0.5	25
			$V_R=650V, T_J=175^{\circ}C$	5	-
Total capacitive charge	Q_C	nC	$V_R=400V, T_J=25^{\circ}C, Q_C=\int_0^{V_R} C(V)dV$	25	-
Total capacitance	C	μF	$V_R=0V, f=1MHz$	378	-
			$V_R=200V, f=1MHz$	51	-
			$V_R=400V, f=1MHz$	49	-
Capacitance Stored Energy	E_C	μJ	$V_R=400V$	3	-

Thermal Characteristics ($T_a=25$ Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	Value
Thermal resistance	R_{J-C}	$^{\circ}C/W$	4.76

Typical Characteristics

Figure 1. Forward CharacterCharacteristi

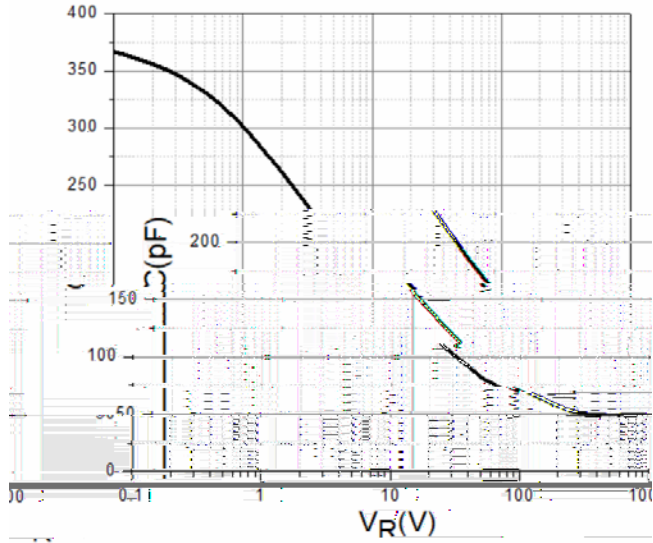


Figure 3. Capacitance vs. Reverse Voltage

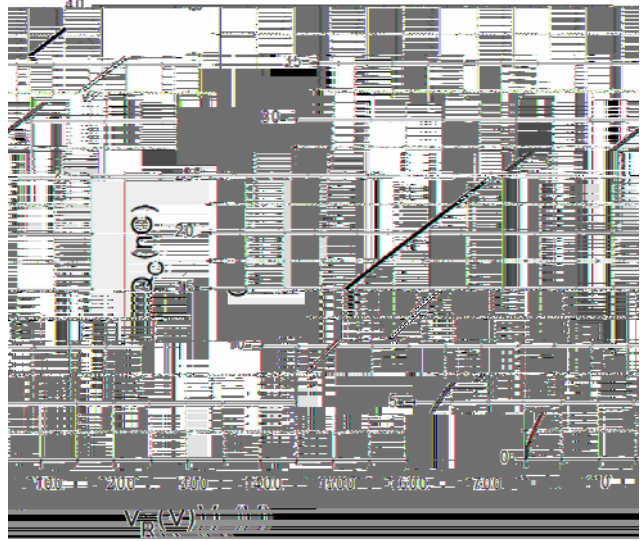


Figure 4. Total Capacitance Charge vs. Reverse Voltage

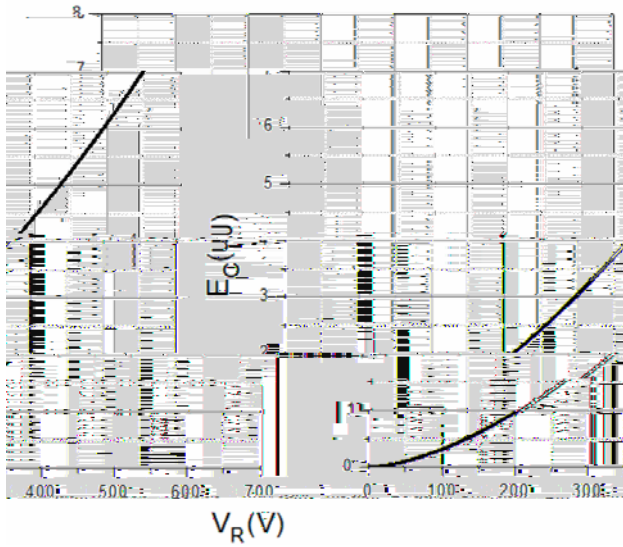


Figure 5. Capacitance Stored Energy

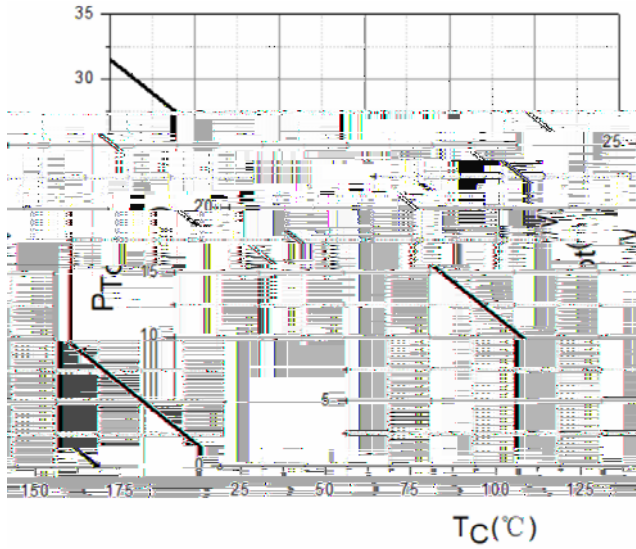


Figure 6. Power Derating

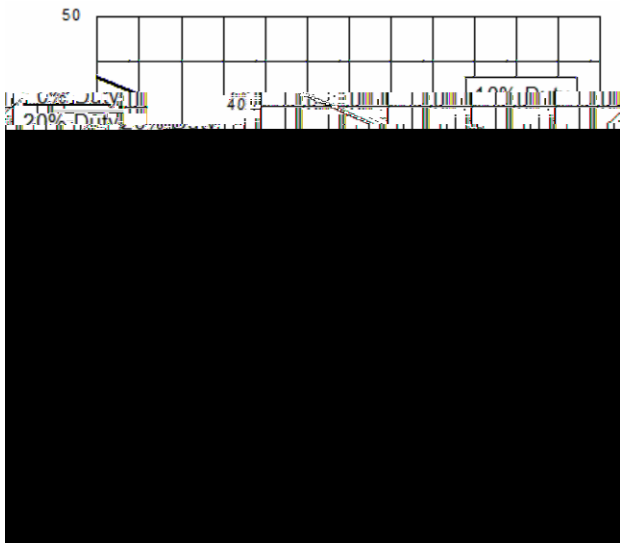


Figure 7. Current Derating

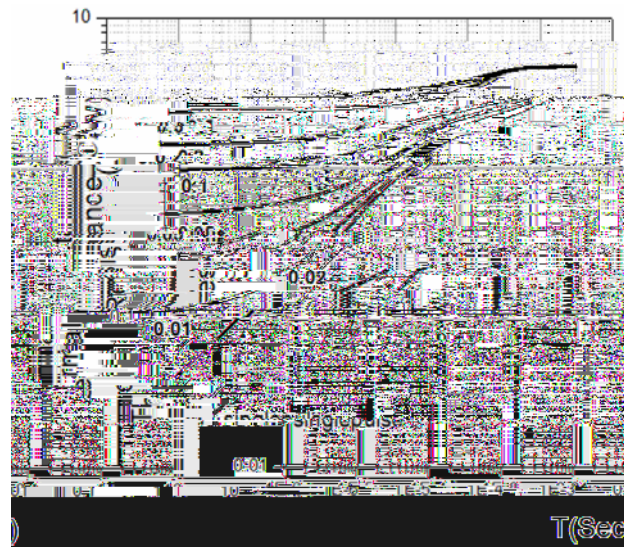
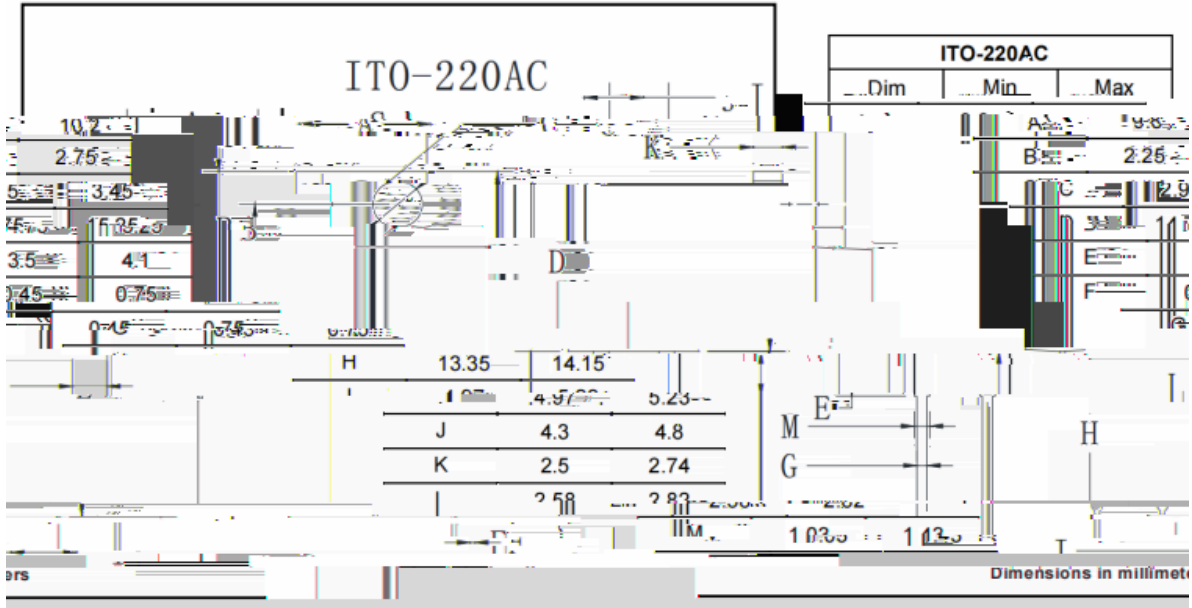


Figure 8. Transient Thermal Impedance



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Outline Dimensions



'LVFODLPHU

7KH LQIRUPDQWRIC \$ QHWKLV GRFXPHQW<DQJRKUR X HIBQJHQZHHF(ROHFOVRUR Q&RF /VHG UHV
ULJKW WR PDNH FKD QJHRU ZW WIK R/XSMIKHRSVLRG XRF Q V R IGWV SFCSDARIGHKUHUCILDEWQGMV L J XQ F
RU RWKHUZLVH

7KH SURGXFW OLVVJCH G HWRI EQ LXV B G VZH FWKURRQG IEQHTUX L S PHQW RU GHYLFHWWKDQG Q
HTXLSPHQW RU GHYLLFHH K IZJKL FKH VHHOGRW K H PLDDEIXOLFWML B Q X B IE QGLEDJHFHUOK XPFKQDQVLIH
PHGLFDO LQVWUXPHQW VIT XLLSDPWSRUFHMDUFAK LQX FOH DU UHDFVKHUO FFROQWUURROOHUW D Q
GHYLFHV <DQJMLHW R LE HDIDRQ HDR/Q XLP H O LQV R UHVVSIRDE/LQEL W/H V R O VDIQQ JGIDJRPJMMFK LP
RI VDOH

7KLV SXEOLFDWLRG SVXSSHHW HDGIVLQURQJPDVXLSRQL HSGHYRUR XDGGLRQL FSOCHD V B WRHJPLW R X
KWVZZ \DQJMLH FRP